

Andrey B Krysa

List of Publications by Year in descending order

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218677

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256
all docs

256
docs citations

256
times ranked

2133
citing authors

#	ARTICLE	IF	CITATIONS
1	Wide bandgap semiconductor conversion devices for radioisotope microbatteries. Materials Science in Semiconductor Processing, 2022, 142, 106533.	4.0	5
2	Coherence in single photon emission from droplet epitaxy and Stranski-Krastanov quantum dots in the telecom C-band. Applied Physics Letters, 2021, 118, .	3.3	34
3	The response of thick ($10\text{--}14\text{ }\mu\text{m}$) AlInP x-ray and I^{137}Cs -ray detectors at up to 88 keV. Journal of Applied Physics, 2021, 129, 243105.	2.5	2
4	X-ray photon counting spectroscopy with an AlInP array. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 1002, 165293.	1.6	1
5	Impact Ionization Coefficients in $\text{Al}_x\text{Ga}_{1-x}\text{Tl}$. Journal of Applied Physics, 2021, 129, 105284.	3.0	3
6	Lattice-Matched to GaAs. IEEE Transactions on Electron Devices, 2021, 68, 4045-4050. InGaP $2\text{ }\mu\text{m}$ pixel array for X-ray and I^{137}Cs -ray spectroscopy. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 1010, 165549.	1.6	2
7	A prototype AlInP electron spectrometer. Planetary and Space Science, 2021, 205, 105284.	1.7	0
8	Quantum Light Emitting Diodes and their Applications. , 2021, , .		0
9	GaAs/Al _{0.8} Ga _{0.2} As separate absorption and multiplication region x-ray spectroscopic avalanche photodiodes. Journal of Applied Physics, 2020, 128, .	2.5	3
10	Monolithic InP Quantum Dot Mode-Locked Lasers Emitting at 730 nm. IEEE Photonics Technology Letters, 2020, 32, 1073-1076.	2.5	7
11	Quantum cascade laser with bound-to-quasi-continuum optical transitions at a temperature of up to 371 K. Quantum Electronics, 2020, 50, 710-713.	1.0	2
12	AlInP X-ray photodiodes without incomplete charge collection noise. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2020, 960, 163606.	1.6	6
13	Gigahertz-Clocked Teleportation of Time-Bin Qubits with a Quantum Dot in the Telecommunication Band. Physical Review Applied, 2020, 13, .	3.8	25
14	MOVPE-Grown Quantum Cascade Laser Structures Studied by Kelvin Probe Force Microscopy. Crystals, 2020, 10, 129.	2.2	1
15	Quantum teleportation using highly coherent emission from telecom C-band quantum dots. Npj Quantum Information, 2020, 6, .	6.7	66
16	Al _{0.6} Ga _{0.4} As x-ray avalanche photodiodes for spectroscopy. Semiconductor Science and Technology, 2020, 35, 095026.	2.0	8
17	1GHz clocked distribution of electrically generated entangled photon pairs. Optics Express, 2020, 28, 36838.	3.4	11
18	InGaAs x-ray photodiode for spectroscopy. Materials Research Express, 2020, 7, 105901.	1.6	1

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19	InGaP electron spectrometer for high temperature environments. Scientific Reports, 2019, 9, 11096.	3.3	3
20	High temperature AlInP X-ray spectrometers. Scientific Reports, 2019, 9, 12155.	3.3	7
21	X-ray spectroscopy with an AlInP photodiode. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 943, 162467.	1.6	5
22	Improved Planar InAs Avalanche Photodiodes With Reduced Dark Current and Increased Responsivity. Journal of Lightwave Technology, 2019, 37, 2375-2379.	4.6	5
23	AlInP photodiode x-ray detectors. Journal Physics D: Applied Physics, 2019, 52, 225101.	2.8	3
24	InP Quantum Dot Mode-Locked Lasers and Materials Studies. , 2019, , .		0
25	12.5-GHz InP Quantum Dot Monolithically Mode-Locked Lasers Emitting at 740 nm. , 2019, , .		0
26	Quantum teleportation using coherent emission from telecom C-band quantum dots. , 2019, , .		0
27	A quantum light-emitting diode for the standard telecom window around 1,550 nm. Nature Communications, 2018, 9, 862.	12.8	119
28	InAs thermophotovoltaic cells with high quantum efficiency for waste heat recovery applications below 1000 Å°C. Solar Energy Materials and Solar Cells, 2018, 179, 334-338.	6.2	44
29	Measurement of the electron-hole pair creation energy in InAs using X-ray r. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2018, 879, 64-68.	1.6	20
30	Energy response characterization of InGaP X-ray detectors. Journal of Applied Physics, 2018, 124, 195704.	2.5	9
31	600 nm thick AlInP ⁵⁵ Fe x-ray photovoltaic and ⁶³ Ni betavoltaic cells. Semiconductor Science and Technology, 2018, 33, 105003.	2.0	4
32	Temperature characterisation of spectroscopic InGaP X-ray photodiodes. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2018, 908, 277-284.	1.6	13
33	Femtosecond Alexandrite laser passively mode-locked by an InP/InGaP quantum-dot saturable absorber. Optics Letters, 2018, 43, 232.	3.3	48
34	Femtosecond Alexandrite Laser with InP/InGaP Quantum-Dot Saturable Absorber. , 2018, , .		1
35	A GaInAs/AlInAs quantum cascade laser with an emission wavelength of 5.6 μm. Quantum Electronics, 2018, 48, 472-475.	1.0	4
36	InP/InGaP quantum-dot SESAM mode-locked Alexandrite laser. , 2018, , .		0

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37	Absorption coefficients in AlGaInP lattice-matched to GaAs. Solar Energy Materials and Solar Cells, 2017, 164, 28-31.	6.2	13
38	Growth scheme for quantum dots with low fine structure splitting at telecom wavelengths (Conference Presentation). , 2017, , .		0
39	Progress in low light-level InAs detectors- towards Geiger-mode detection. , 2017, , .		0
40	Transmission electron microscopy of AlGaAs/GaAs quantum cascade laser structures. Journal of Microscopy, 2017, 268, 298-304.	1.8	7
41	Investigation of a temperature tolerant InGaP (GaInP) converter layer for a ⁶³ Ni betavoltaic cell. Journal Physics D: Applied Physics, 2017, 50, 345101.	2.8	10
42	InGaP (GaInP) mesa p-i-n photodiodes for X-ray photon counting spectroscopy. Scientific Reports, 2017, 7, 10206.	3.3	11
43	Temperature effects on an InGaP (GaInP) ⁵⁵ Fe X-ray photovoltaic cell. Scientific Reports, 2017, 7, 4981.	3.3	7
44	Universal Growth Scheme for Quantum Dots with Low Fine-Structure Splitting at Various Emission Wavelengths. Physical Review Applied, 2017, 8, .	3.8	53
45	Growth scheme for quantum dots with low fine structure splitting at telecom wavelengths. , 2017, , .		0
46	InAsP/AlGaInP/GaAs QD laser operating at $\lambda \approx 770$ nm. Journal of Physics: Conference Series, 2016, 740, 012008.	0.4	7
47	Temperature dependence of an AlInP ⁶³ Ni betavoltaic cell. Journal of Applied Physics, 2016, 120, 144501.	2.5	9
48	Al _{0.52} In _{0.48} P ⁵⁵ Fe x-ray-photovoltaic battery. Journal Physics D: Applied Physics, 2016, 49, 355601.	2.8	18
49	Growth and characterisation of InAsP/AlGaInP QD laser structures. , 2016, , .		1
50	High sensitivity InAs photodiodes for mid-infrared detection. , 2016, , .		2
51	Tuning Nonlinear Mechanical Mode Coupling in GaAs Nanowires Using Cross-Section Morphology Control. Nano Letters, 2016, 16, 7414-7420.	9.1	13
52	Temperature study of Al _{0.52} In _{0.48} P detector photon counting X-ray spectrometer. Journal of Applied Physics, 2016, 120, .	2.5	10
53	Al _{0.52} In _{0.48} P avalanche photodiodes for soft X-ray spectroscopy. Journal of Instrumentation, 2016, 11, P03021-P03021.	1.2	17
54	Characterisation of Al _{0.52} In _{0.48} P mesa p-i-n photodiodes for X-ray photon counting spectroscopy. Journal of Applied Physics, 2016, 120, 024502.	2.5	14

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55	Visible light communication using InGaN optical sources with AlInGaP nanomembrane down-converters. Optics Express, 2016, 24, 10020.	3.4	11
56	High-Gain InAs Planar Avalanche Photodiodes. Journal of Lightwave Technology, 2016, 34, 2639-2644.	4.6	8
57	Avalanche Noise in Al _{0.52} In _{0.48} P Diodes. IEEE Photonics Technology Letters, 2016, 28, 481-484.	2.5	5
58	Mechanism for enhanced wavelength tuning in gain-enhanced InP quantum dot lasers. IET Optoelectronics, 2016, 10, 66-69.	3.3	1
59	Laser-excited 580nm AlGaInP nanomembrane for visible light communications. , 2016, , .		1
60	InAsP quantum dot lasers. , 2015, , .		0
61	InAsP quantum dot lasers grown by MOVPE. Optics Express, 2015, 23, 27282.	3.4	16
62	MQW nanomembrane assemblies for visible light communications. , 2015, , .		1
63	Determination of absorption coefficients in AlInP lattice matched to GaAs. Journal Physics D: Applied Physics, 2015, 48, 405101.	2.8	12
64	A high sensitivity detector for underwater communication systems. Proceedings of SPIE, 2015, , .	0.8	0
65	Linearly Polarized Emission from an Embedded Quantum Dot Using Nanowire Morphology Control. Nano Letters, 2015, 15, 1559-1563.	9.1	37
66	Twinning in GaAs nanowires on patterned GaAs(111)B. Crystal Research and Technology, 2015, 50, 62-68.	1.3	3
67	Effect of thermal carrier spreading on the temperature dependence of threshold current in InP quantum dot lasers. Proceedings of SPIE, 2015, , .	0.8	0
68	Exploring the wavelength range of InP/AlGaInP QDs and application to dual-state lasing. Semiconductor Science and Technology, 2015, 30, 044002.	2.0	10
69	Reducing Thermal Carrier Spreading in InP Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 668-673.	2.9	10
70	Effects of temperature and difference-wavelength on mode stability in Dual-λ QD lasers. Proceedings of SPIE, 2015, , .	0.8	0
71	InAs Photodiodes for 3.43 μm Radiation Thermometry. IEEE Sensors Journal, 2015, 15, 5555-5560.	4.7	15
72	The Effect on Dot Gain Behaviour of Confining Layer Composition in InP/(Al)GaInP Quantum Dot Lasers. , 2015, , .		0

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73	External Cavity Quantum Cascade Laser Based on Fabry-Pérot Reflector. , 2015, , .		0
74	Opening up spectrum with InPAs quantum dot lasers. , 2015, , .		0
75	Al _{0.52} In _{0.48} P photodetectors for underwater communication systems. , 2015, , .		0
76	A Rapid Swept-Source Mid-Infrared Laser. , 2014, , .		1
77	Narrow-band detector for underwater communication system. , 2014, , .		1
78	Catalyst-free, III-V nanowire photovoltaics. , 2014, , .		0
79	Lasing Output and Threshold Current Density in P-Doped InP/AlGaInP Quantum Dot Laser Diodes. , 2014, , .		0
80	Improved laser performance in NIR InP Dot Based Structures with Strained Layers. , 2014, , .		0
81	The Effects of Temperature and Difference-Wavelength on Mode Stability in Dual-Mode QD Lasers. , 2014, , .		0
82	Dual-wavelength InP quantum dot lasers. Applied Physics Letters, 2014, 104, .	3.3	14
83	Temperature dependence of avalanche multiplication and breakdown voltage in Al _{0.52} In _{0.48} P. Journal of Applied Physics, 2014, 115, .	2.5	9
84	Al _{0.52} In _{0.48} P SAM-APD as a Blue-Green Detector. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 142-146.	2.9	20
85	Element-sensitive measurement of the hole-nuclear spin interaction in quantum dots. Nature Physics, 2013, 9, 74-78.	16.7	70
86	Absorption, Gain, and Threshold in InP/AlGaInP Quantum Dot Laser Diodes. IEEE Journal of Quantum Electronics, 2013, 49, 389-394.	1.9	7
87	Homogeneous Array of Nanowire-Embedded Quantum Light Emitters. Nano Letters, 2013, 13, 861-865.	9.1	40
88	Design of high sensitivity detector for underwater communication system. , 2013, , .		3
89	InP quantum dot lasers with temperature insensitive operating wavelength. Applied Physics Letters, 2013, 103, .	3.3	12
90	Low temperature threshold current density effect by p-doping in InP/AlGaInP quantum dot laser diodes. , 2013, , .		0

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91	Mode stability and wavelength selection in dual- λ QD lasers. , 2013, , .		0
92	Intensity stability and wavelength separation in dual- λ QD lasers. , 2013, , .		0
93	Wavelength Selection and Temperature Tuning in Dual- λ QD lasers. , 2013, , .		0
94	The effect of p-doping in InP/AlGaInP quantum dot lasers. , 2012, , .		0
95	Spectroscopic study of transparency current in mid-infrared quantum cascade lasers. Optics Express, 2012, 20, 18925.	3.4	2
96	P-doped effect on dot density in InP/AlGaInP laser diode structures. , 2012, , .		0
97	The effect of strained confinement layers in InP self-assembled quantum dot material. Semiconductor Science and Technology, 2012, 27, 094008.	2.0	13
98	Direct Determination of Transparency Current in Mid-Infrared Quantum Cascade Laser. , 2012, , .		0
99	Strained confinement layers in InP quantum dot lasers. , 2012, , .		2
100	Achieving temperature-insensitive λ in InP quantum dot lasers. , 2012, , .		0
101	700nm InP quantum dot lasers with strained confinement layers. , 2012, , .		0
102	Dual- λ InP/AlGaInP quantum dot laser. , 2012, , .		0
103	InAs electron avalanche photodiodes with 580 GHz gain-bandwidth product. , 2012, , .		2
104	Structural analysis of strained quantum dots using nuclear magnetic resonance. Nature Nanotechnology, 2012, 7, 646-650.	31.5	65
105	Room-Temperature GaAs/AlGaAs Quantum Cascade Lasers Grown by Metal-Organic Vapor Phase Epitaxy. IEEE Photonics Technology Letters, 2011, 23, 774-776.	2.5	10
106	Dot Density Effect by Quantity of Deposited Material in InP/AlGaInP Structures. IEEE Photonics Technology Letters, 2011, 23, 1169-1171.	2.5	9
107	Impact Ionization Coefficients in $\text{Al}_{0.52}\text{In}_{0.48}\text{P}$. IEEE Electron Device Letters, 2011, 32, 1528-1530.	3.9	14
108	High Repetition Rate Ti:Sapphire Laser Mode-Locked by InP Quantum-Dot Saturable Absorber. IEEE Photonics Technology Letters, 2011, 23, 1603-1605.	2.5	10

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109	Carrier distribution in InP/AlGaInP quantum dot laser diodes. , 2011, , .		0
110	Direct Measurement of the Hole-Nuclear Spin Interaction in Single InP/GaInP Quantum Dots Using Photoluminescence Spectroscopy. Physical Review Letters, 2011, 106, 027402.	7.8	93
111	High speed InAs electron avalanche photodiodes overcome the conventional gain-bandwidth product limit. Optics Express, 2011, 19, 23341.	3.4	95
112	Charge control in InP/(Ga,In)P single quantum dots embedded in Schottky diodes. Physical Review B, 2011, 84, .	3.2	13
113	Passively Q-switched Pr:YLF laser. , 2011, , .		8
114	Vertical Sub-Wavelength Mode Confinement in THz Quantum Cascade Lasers. , 2011, , .		0
115	Room Temperature GaAs/AlGaAs Quantum Cascade Lasers with InGaP and InAlP Waveguides. , 2011, , .		0
116	Deep etched distributed Bragg reflector (DBR) InP/AlGaInP quantum dot lasers. , 2011, , .		1
117	Purcell-enhanced single-photon emission from an InP quantum dot coupled to GaInP photonic crystal nanocavity. Proceedings of SPIE, 2011, , .	0.8	0
118	Origin of the temperature dependence of threshold current in InP/AlGaInP quantum dot lasers. , 2011, , .		3
119	Temperature Dependence of Leakage Current in InAs Avalanche Photodiodes. IEEE Journal of Quantum Electronics, 2011, 47, 1123-1128.	1.9	43
120	Temperature-Dependent Threshold Current in InP Quantum-Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1343-1348.	2.9	15
121	InP-Based Midinfrared Quantum Cascade Lasers for Wavelengths Below $4\frac{1}{4}\mu\text{m}$. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1417-1425.	2.9	15
122	Time-domain spectroscopy of mid-infrared quantum cascade lasers. Semiconductor Science and Technology, 2011, 26, 014020.	2.0	0
123	Recent progress in short wavelength quantum cascade lasers. , 2011, , .		2
124	Quantum dot lasers - the role of the 2D states. , 2011, , .		0
125	Light-polarization-independent nuclear spin alignment in a quantum dot. Physical Review B, 2011, 83, .	3.2	11
126	Vertical subwavelength mode confinement in terahertz and mid-infrared quantum cascade lasers. Applied Physics Letters, 2011, 98, .	3.3	22

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127	Low threshold room temperature GaAs/AlGaAs quantum cascade laser with InAlP waveguide. Electronics Letters, 2011, 47, 1193.	1.0	4
128	High temperature $\lambda = 4 \mu\text{m}$ In _{0.7} Ga _{0.3} As/In _{0.34} Al _{0.66} As quantum cascade lasers grown by MOVPE. Electronics Letters, 2011, 47, 559.	1.0	2
129	High performance short wavelength InP-based quantum cascade lasers. , 2010, , .		0
130	STEM imaging of InP/AlGaInP quantum dots. Journal of Physics: Conference Series, 2010, 245, 012087.	0.4	3
131	Growth of low density InP/GaInP quantum dots. Journal of Physics: Conference Series, 2010, 245, 012061.	0.4	3
132	Optimization of low density InP/GaInP quantum dots for single-dot studies. Journal of Physics: Conference Series, 2010, 245, 012093.	0.4	2
133	Short Wavelength InP Based Quantum Cascade Lasers. , 2010, , .		1
134	Ultrafast Spectroscopy As A Probe Of Light-Matter Interaction In A Midinfrared Quantum Cascade Laser. , 2010, , .		0
135	Pumping of Nuclear Spins by Optical Excitation of Spin-Forbidden Transitions in a Quantum Dot. Physical Review Letters, 2010, 104, 066804.	7.8	61
136	Control of spontaneous emission from InP single quantum dots in GaInP photonic crystal nanocavities. Applied Physics Letters, 2010, 97, 181104.	3.3	13
137	$\lambda = 3.36 \mu\text{m}$ room temperature InGaAs/AlAs(Sb) quantum cascade lasers with third order distributed feedback grating. Applied Physics Letters, 2010, 97, 111113.	3.3	3
138	Dynamics of optically induced nuclear spin polarization in individual $\text{InP} \times \text{Ga} \times \text{InP}$ dots. Physical Review B, 2010, 81, .	3.2	28
139	Ultrafast gain dynamics in InP quantum-dot optical amplifiers. Applied Physics Letters, 2010, 97, 211103.	3.3	13
140	Effect of Growth Temperature on InP QD Lasers. IEEE Photonics Technology Letters, 2010, 22, 88-90.	2.5	12
141	Passive Mode-Locking of a Ti:Sapphire Laser by InGaP Quantum-Dot Saturable Absorber. IEEE Photonics Technology Letters, 2010, 22, 209-211.	2.5	19
142	High-Peak-Power Room-Temperature $\lambda = 3.6 \mu\text{m}$ InGaAs/AlAs(Sb) Quantum Cascade Lasers. IEEE Photonics Technology Letters, 2010, 22, 757-759.	2.5	2
143	Transmission Properties of Plasmonic Metamaterial Quantum Cascade Lasers. IEEE Photonics Technology Letters, 2010, 22, 1217-1219.	2.5	3
144	Room-Temperature Operation of Discrete-Mode InGaAs/AlAsSb Quantum-Cascade Laser With Emission at $\lambda = 3.3 \mu\text{m}$. IEEE Photonics Technology Letters, 2010, 22, 1273-1275.	2.5	7

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145	Room temperature $\approx 3.3 \mu\text{m}$ InP-based InGaAs/AlAs(Sb) quantum cascade lasers. Electronics Letters, 2010, 46, 439.	1.0	6
146	High peak power ≈ 3.3 and $3.5 \mu\text{m}$ InGaAs/AlAs(Sb) quantum cascade lasers operating up to 400 K. Applied Physics Letters, 2010, 97, .	3.3	35
147	Dot state distribution, gain and threshold in 700nm band InP/AlGaInP quantum dot lasers. , 2010, , .		0
148	Semiconductor Disk Lasers Incorporating InP/GaInP Quantum Dots for 716-755 nm Emission. , 2010, , .		0
149	InP/AlGaInP 730nm Emission Quantum Dot Lasers. , 2009, , .		0
150	InP/GaInP quantum dot semiconductor disk laser for TEM ₀₀ emission at 740 nm. , 2009, , .		0
151	Analysis of sub-picosecond mid-infrared pulse propagation in a quantum cascade laser below and above threshold. , 2009, , .		0
152	Probing diagonal laser transitions in InGaAs/AlInAs/InP quantum cascade lasers. Journal of Applied Physics, 2009, 106, .	2.5	1
153	High performance, high temperature $\approx 3.7 \mu\text{m}$ InGaAs/AlAs(Sb) quantum cascade lasers. Applied Physics Letters, 2009, 95, 111113.	3.3	14
154	Operating Characteristics of GaAs/InGaP Self Aligned Stripe Lasers. Japanese Journal of Applied Physics, 2009, 48, 04C120.	1.5	1
155	Intersubband gain-induced dispersion. Optics Letters, 2009, 34, 208.	3.3	8
156	InP/AlGaInP quantum dot semiconductor disk lasers for CW TEM ₀₀ emission at 716 – 755 nm. Optics Express, 2009, 17, 21782.	3.4	39
157	$\approx 3.1 \mu\text{m}$ room temperature InGaAs/AlAsSb/InP quantum cascade lasers. Applied Physics Letters, 2009, 94, .	3.3	55
158	Barrier width and growth temperature effect in InP/AlGaInP quantum dot lasers. , 2009, , .		0
159	Effect of temperature on threshold current density in InP/AlGaInP quantum dot laser structures. International Journal of Nano and Biomaterials, 2009, 2, 147.	0.1	2
160	Higher power density limit at COMD in GaInP/AlGaInP in quantum dots than in wells. , 2009, , .		2
161	Room Temperature InGaAs-AlAsSb Quantum Cascade Lasers Operating in 3 – 4 μm Range. , 2009, , .		1
162	Femtosecond Dynamics of a Midinfrared Quantum Cascade Laser. , 2009, , .		0

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163	Intracavity near-field optical imaging of a mid-infrared quantum cascade laser mode. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 149, 270-274.	3.5	3
164	Ultrafast phase-resolved pump-probe measurements on a quantum cascade laser. Applied Physics Letters, 2008, 93, 151106.	3.3	26
165	IEEE 802.11a Data Over Fiber Transmission Using Electromagnetic Bandgap Photonic Antenna With Integrated Asymmetric Fabry-Pérot Modulator/Detector. Journal of Lightwave Technology, 2008, 26, 2671-2678.	4.6	2
166	Proof-of-principle of surface detection with air-guided quantum cascade lasers. Optics Express, 2008, 16, 6387.	3.4	7
167	GaAs-based self-aligned laser incorporating InGaP opto-electronic confinement layer. Electronics Letters, 2008, 44, 905.	1.0	13
168	Single grating period quantum cascade laser array with broad wavelength tuning range. Electronics Letters, 2008, 44, 1306.	1.0	1
169	Higher catastrophic optical mirror damage power density level at facet from quantum dot material. , 2008, , .		3
170	Ultrafast probing of light-matter interaction in a midinfrared quantum cascade laser. Applied Physics Letters, 2008, 93, 091105.	3.3	18
171	InP / AlGaInP short wavelength quantum dot lasers. , 2008, , .		0
172	Overhauser effect in individual $\text{In}_{1-x}\text{Ga}_x\text{In}$ dots. Physical Review B, 2008, 77, .	3.2	27
173	GaAs-based buried heterostructure laser incorporating an InGaP opto-electronic confinement layer. , 2008, , .		0
174	Short-wavelength quantum cascade lasers. , 2008, , .		1
175	Ultrafast probing of the complex refractive index in an active mid infrared quantum cascade laser. , 2008, , .		0
176	Time resolved spectroscopy of dynamics in mid infrared quantum cascade lasers below and above threshold. , 2007, , .		0
177	<title>Laser CRT as a light source for display technology</title>. , 2007, , .		0
178	Laser cathode-ray tube with a monolithic laser screen. Quantum Electronics, 2007, 37, 853-856.	1.0	3
179	Quantum Cascade Microdisk Lasers for Mid Infrared Intra-Cavity Sensing. , 2007, , .		1
180	Fingerprints of spatial charge transfer in quantum cascade lasers. Journal of Applied Physics, 2007, 102, .	2.5	32

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181	InGaAs-AlAsSb quantum cascade lasers: towards 3 μ m emission. , 2007, , .		0
182	Dead-space corrected GaInP/GaAs composite collector double heterojunction bipolar transistors. Journal of Applied Physics, 2007, 101, 086111.	2.5	0
183	Fabrication and Characterization of InP-Based Quantum Cascade Distributed Feedback Lasers with Inductively Coupled Plasma Etched Lateral Gratings. Japanese Journal of Applied Physics, 2007, 46, 2424-2428.	1.5	1
184	Optical mode control of surface-plasmon quantum cascade lasers. AIP Conference Proceedings, 2007, , .	0.4	0
185	Room-temperature operation of mid-infrared surface-plasmon quantum cascade lasers. AIP Conference Proceedings, 2007, , .	0.4	0
186	Demonstration of air-guided quantum cascade lasers without top claddings. Optics Express, 2007, 15, 14861.	3.4	12
187	Single-photon avalanche diode detectors for quantum key distribution. IET Optoelectronics, 2007, 1, 249-254.	3.3	11
188	InGaAs \cdot AlAsSb \cdot InP strain compensated quantum cascade lasers. Applied Physics Letters, 2007, 90, 151105.	3.3	17
189	Improved performance of In _{0.6} Ga _{0.4} As \cdot AlAs _{0.67} Sb _{0.33} \cdot InP quantum cascade lasers by introduction of AlAs barriers in the active regions. Applied Physics Letters, 2007, 91, 051123.	3.3	15
190	Direct imaging of a laser mode via midinfrared near-field microscopy. Applied Physics Letters, 2007, 90, 201114.	3.3	11
191	InP/AlGaInP on GaAs Quantum Dot Lasers. , 2007, , .		0
192	Integrated Photonic Electromagnetic Band Gap Antenna with InGaAs/AlInGaAs Multiple Quantum Well Asymmetric Fabry-Perot Modulator. , 2007, , .		3
193	InGaAs \cdot AlAsSb \cdot InP quantum cascade lasers operating at wavelengths close to $3\frac{1}{4}$ μ m. Applied Physics Letters, 2007, 90, 021108.	3.3	89
194	Low threshold InP/AlGaInP on GaAs QD laser emitting at λ \approx 740nm. Journal of Crystal Growth, 2007, 298, 663-666.	1.5	15
195	Characterization of intersubband devices combining a nonequilibrium many body theory with transmission spectroscopy experiments. Journal of Materials Science: Materials in Electronics, 2007, 18, 689-694.	2.2	29
196	Intersubband spectroscopy of quantum cascade lasers under operating conditions. Applied Physics Letters, 2006, 88, 131105.	3.3	21
197	All-electrical, room temperature surface plasmon generation using quantum cascade lasers. , 2006, , .		0
198	Design and Performance of an InGaAs \cdot InP Single-Photon Avalanche Diode Detector. IEEE Journal of Quantum Electronics, 2006, 42, 397-403.	1.9	120

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199	Enhanced linear dynamic range of asymmetric Fabry-Pe/spl acute/rot modulator/detector. IEEE Photonics Technology Letters, 2006, 18, 770-772.	2.5	5
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